# **Amplifier Transistor**

### **NPN Silicon**

#### **Features**

• These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	80	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	80	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	Vdc
Collector Current - Continuous	I <sub>C</sub>	500	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

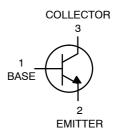
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1.  $FR-5 = 1.0 \times 0.75 \times 0.062 \text{ in.}$
- 2. Alumina = 0.4 X 0.3 X 0.024 in. 99.5% alumina.



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SOT-23 (TO-236) CASE 318 STYLE 6

#### **MARKING DIAGRAM**



KB = Specific Device Code

M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)
\*Date Code orientation and/or overbar may
vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

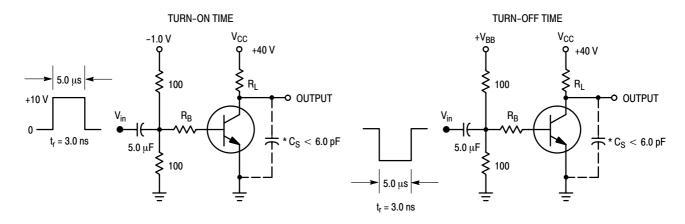
Device	Package	Shipping <sup>†</sup>
MMBT8099LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	<u>.</u>			
Collector – Emitter Breakdown Voltage (Note 3) (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	80	_	Vdc
Collector – Base Breakdown Voltage (I <sub>C</sub> = 100 µAdc, I <sub>E</sub> = 0)	V <sub>(BR)</sub> CBO	80	-	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 10 \mu Adc, I_C = 0$ )	V <sub>(BR)EBO</sub>	6.0	-	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 60 Vdc, I <sub>B</sub> = 0)	I <sub>CES</sub>	-	0.1	μAdc
Collector Cutoff Current $(V_{CB} = 60 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 80 \text{ Vdc}, I_E = 0)$	Ісво	- -	0.1 -	μAdc
Emitter Cutoff Current $(V_{EB} = 6.0 \text{ Vdc}, I_C = 0)$ $(V_{EB} = 4.0 \text{ Vdc}, I_C = 0)$	I <sub>EBO</sub>	- -	0.1 -	μAdc
ON CHARACTERISTICS (Note 3)	·			
DC Current Gain	h <sub>FE</sub>	100 100 75	300 - -	-
Collector – Emitter Saturation Voltage ( $I_C = 100 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ ) ( $I_C = 100 \text{ mAdc}$ , $I_B = 10 \text{ mAdc}$ )	V <sub>CE(sat)</sub>	_ _	0.4 0.3	Vdc
Base-Emitter On Voltage ( $I_C = 1.0 \text{ mAdc}$ , $V_{CE} = 5.0 \text{ Vdc}$ ) ( $I_C = 10 \text{ mAdc}$ , $V_{CE} = 5.0 \text{ Vdc}$ )	V <sub>BE(on)</sub>	_ 0.6	_ 0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current – Gain – Bandwidth Product (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 100 MHz)	fr	150	_	MHz
Output Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	_	6.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	-	25	pF

<sup>3.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.



\*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

**Figure 1. Switching Time Test Circuits** 

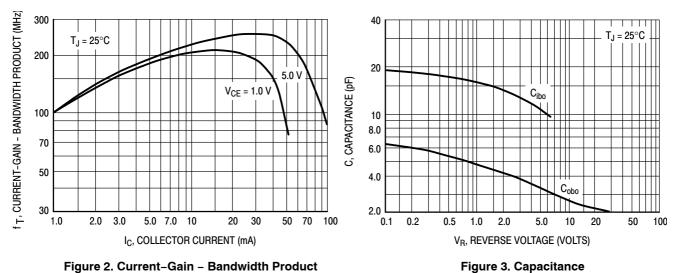


Figure 2. Current-Gain - Bandwidth Product

1.0 k

700

500

300

200

70

50

30

20

10

10

t, TIME (ns) 100  $V_{CC} = 40 \text{ V}$ 

 $I_{\rm C}/I_{\rm B}=10$ 

 $I_{B1} = I_{B2}$ 

 $T_J = 25^{\circ}C$ 

 $t_d @ V_{BE(off)} = 0.5 V$ 

20

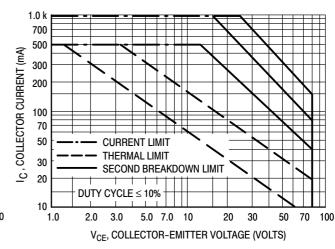


Figure 4. Switching Times

50



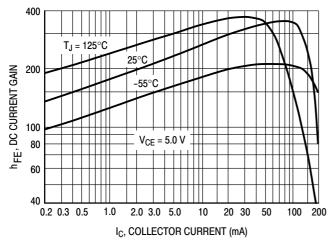


Figure 6. DC Current Gain

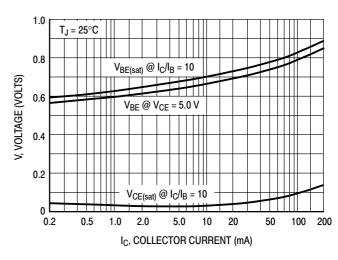


Figure 7. "ON" Voltages

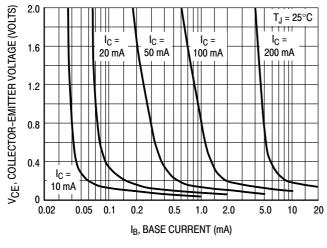


Figure 8. Collector Saturation Region

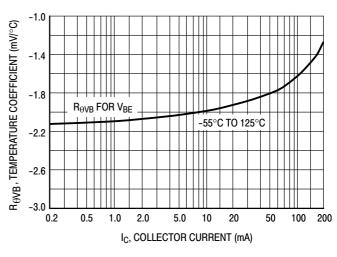


Figure 9. Base-Emitter Temperature Coefficient

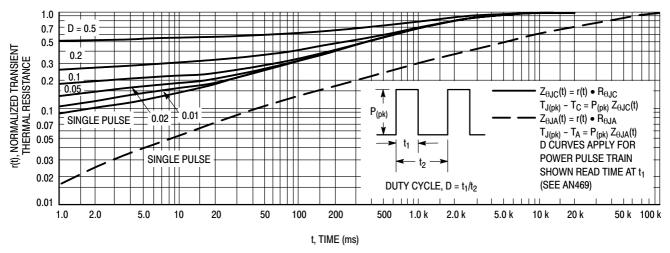
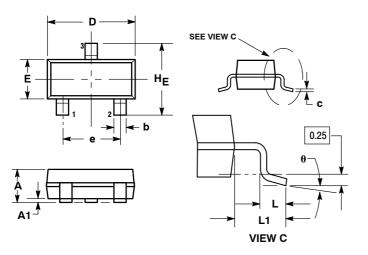


Figure 10. Thermal Response

#### PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AN



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

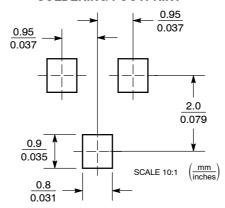
	MILLIMETERS		INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

#### STYLE 6:

PIN 1. BASE

- 2. EMITTER
- 3. COLLECTOR

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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